



DMJ70H600SH3

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	RDS(ON) Max	Ι _D T _C = +25°C	
700V	$0.6\Omega @ V_{GS} = 10V$	11A	

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Backlighting
- AC-DC Converters

Features and Benefits

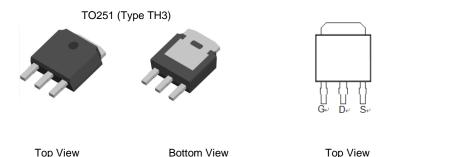
- Low On-Resistance
- High BV_{DSS} Rating for Power Application
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: TO251 (Type TH3)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)

G

• Weight: 0.33 grams (Approximate)



Top View Pin Configuration

Internal Schematic

S

D

Ordering Information (Note 4)

Part Number	Case	Packaging
DMJ70H600SH3	TO251 (Type TH3)	75 Pieces / Tube

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

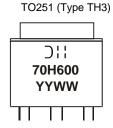
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	700	V	
Gate-Source Voltage		V _{GSS}	±30	V
Continuous Drain Current (Note 5) V_{GS} = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	Ι _D	11 7	A
Maximum Body Diode Forward Current (Note 6)		ls	1.8	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		IDM	11	A
Avalanche Current (Note 7)	L = 60mH	I _{AS}	1.5	A
Avalanche Energy (Note 7)	L = 60mH	E _{AS}	67.5	mJ
Peak Diode Recovery dv/dt (Note 7)	·	dv/dt	5	V/ns

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _C = +25°C	D	113	w
Total Power Dissipation (Note 5)	T _C = +100°C	PD	45	
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	57	°C/W	
Thermal Resistance, Junction to Case (Note 5)	R _{θJC}	1.1		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	700	—		V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} = 700V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	—	100	nA	$V_{GS} = \pm 30V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	2	2.9	4	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	0.5	0.6	Ω	$V_{GS} = 10V, I_D = 2.4A$	
Diode Forward Voltage	V _{SD}	_	0.9	1.2	V	$V_{GS} = 0V, I_{S} = 4.6A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	_	643	_		V _{DS} = 25V, f = 1MHz, V _{GS} = 0V	
Output Capacitance	C _{oss}	_	524		pF		
Reverse Transfer Capacitance	C _{rss}	_	13.5				
Gate Resistance	Rg	_	3.6		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg	_	18.2				
Gate-Source Charge	Q _{gs}		2.5		nC	$V_{DD} = 380V, I_D = 4.6A,$	
Gate-Drain Charge	Q _{gd}	_	8.5			$V_{GS} = 10V$	
Turn-On Delay Time	t _{D(ON)}	_	11	_			
Turn-On Rise Time	t _R	_	22		1	V _{DD} = 380V, V _{GS} = 10V,	
Turn-Off Delay Time	t _{D(OFF)}	_	85	—	ns	$R_g = 25\Omega, I_D = 4.6A$	
Turn-Off Fall Time	t _F	_	23				
Body Diode Reverse Recovery Time	t _{RR}	_	193		ns		
Body Diode Reverse Recovery Charge	Q _{RR}	_	1.6		μC	$I_{S} = 4A, dI/dt = 100A/\mu s$	

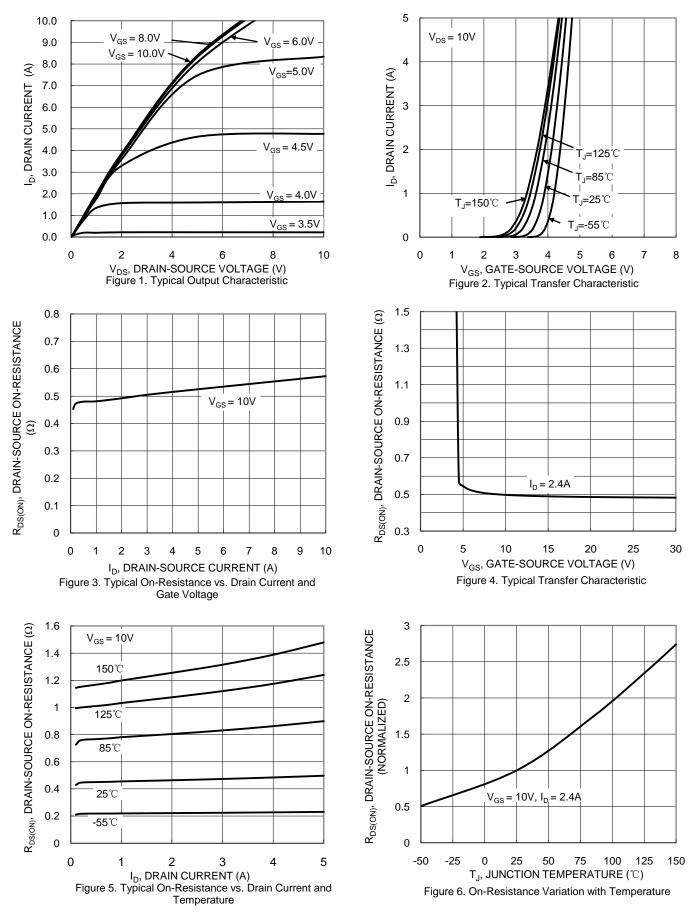
5. Device mounted on infinite heatsink. Notes:

6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Guaranteed by design. Not subject to production testing.
Short duration pulse test used to minimize self-heating effect.



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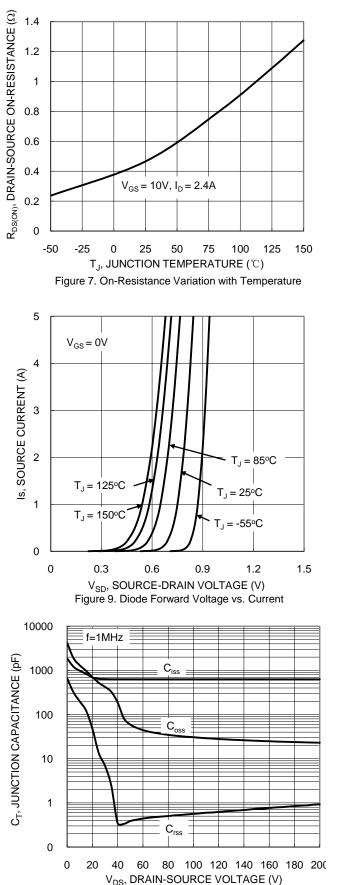
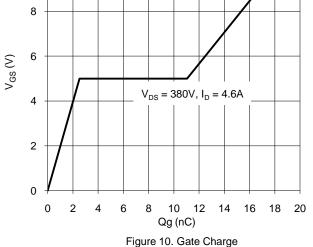
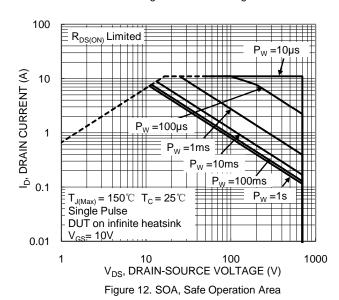


Figure 11. Typical Junction Capacitance

4 V_{GS(TH)}, GATE THRESHOLD VOLTAGE (V) 3.5 $I_D = 1mA$ 3 2.5 $I_{\rm D} = 250 \mu A$ 2 1.5 1 0.5 0 -50 -25 0 25 50 75 100 125 150 T_J, JUNCTION TEMPERATURE (℃) Figure 8. Gate Threshold Variation vs. Junction Temperature 10 8

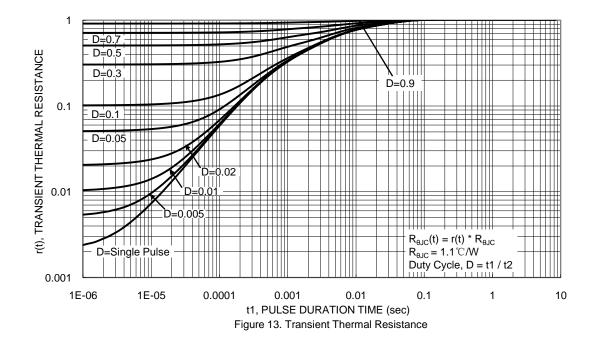




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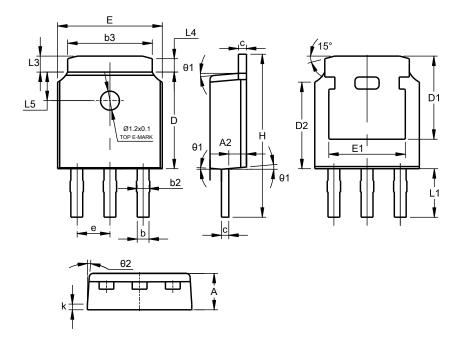




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO251 (Type TH3)



	TO251 (Type TH3)					
Dim	Min	Max	Тур			
Α	2.20	2.40	2.30			
A2	0.97	1.17	1.07			
b	0.68	0.90	0.78			
b2	0.76	0.95	0.84			
b3	5.20	5.50	5.33			
С	0.43	0.63	0.53			
D	5.98	5.98 6.22				
D1	5	5.30 REF				
D2	5.26	5.66	5.46			
е	2.286 BSC					
Е	6.40	6.40 6.80				
E1	4.63	5.03	4.83			
Н	9.40	9.85	9.62			
k	0).40REI	F			
L1	2.30	2.70	2.50			
L3	0.88	1.28	1.02			
L4	0.75 REF					
L5	1.65	1.95	1.80			
θ1	5°	9°	7°			
θ2	5°	9°	7°			
All Dimensions in mm						



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